L Number	Hits	Search Text	DB	Time stamp
1 .	520	(CMP or polishing) with (slurry and water)	EPO; JPO;	2004/08/23 09:19
			DERWENT;	
			IBM_TDB	2004/00/22 00:40
2	1075183	semiconductor or "integrated circuit"	EPO; JPO; DERWENT;	2004/08/23 09:19
1			IBM_TDB	
3	249	((CMP or polishing) with (slurry and water)) and	EPO; JPO;	2004/08/23 09:24
		(semiconductor or "integrated circuit")	DERWENT;	200 1700/20 00:21
1		(combondation or integrated should	IBM TDB	
4	24	438/for.111.ccls.	EPO; JPO;	2004/08/23 09:24
ļ			DERWENT;	
			IBM_TDB	
5	1	((CMP or polishing) with (slurry and water)) and	EPO; JPO;	2004/08/23 09:24
]		438/for.111.ccls.	DERWENT;	
	1006	420/602 colo	IBM_TDB USPAT;	2004/08/19 11:21
-	1906	438/692.ccls.	US-PGPUB	2004/00/19 11.21
	2943	(CMP or polishing) with (slurry and water)	USPAT;	2004/08/23 09:18
	2070	(Sim 5. ponoring) that (Sidily and Hator)	US-PGPUB	
-	447	438/692.ccls. and ((CMP or polishing) with (slurry and water))	USPAT;	2004/08/19 10:41
			US-PGPUB	
-	439	(438/692.ccls. and ((CMP or polishing) with (slurry and water)))	USPAT;	2004/08/19 10:45
		not (@ad>20030901 or @rlad>20030901)	US-PGPUB	0004/00/40 40 4
-	1835	(CMP or polishing) with (slurry with water)	USPAT; US-PGPUB	2004/08/19 10:47
	295	438/692.ccls. and ((CMP or polishing) with (slurry with water))	USPAT;	2004/08/19 10:47
-	295	430/092.ccis. and ((Civir or polishing) with (sturry with water))	US-PGPUB	2004/00/19 10.47
_	291	(438/692.ccls. and ((CMP or polishing) with (slurry with	USPAT;	2004/08/19 11:10
-	20.1	water))) not (@ad>20030901 or @rlad>20030901)	US-PGPUB	
-	761790	dielectric or insulator or oxide or IMD or FSG or USG or TEOS	USPAT;	2004/08/19 11:11
			US-PGPUB	
-	451	((CMP or polishing) with (slurry with water)) with (dielectric or	USPAT;	2004/08/19 11:23
		insulator or oxide or IMD or FSG or USG or TEOS)	US-PGPUB	0004/00/40 44 44
-	65	438/692.ccls. and (((CMP or polishing) with (slurry with water))	USPAT; US-PGPUB	2004/08/19 11:11
		with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS))	US-PGPUB	,
_	65	(438/692.ccls. and (((CMP or polishing) with (slurry with	USPAT;	2004/08/19 11:11
	00	water)) with (dielectric or insulator or oxide or IMD or FSG or	US-PGPUB	
		USG or TEOS))) not (@ad>20030901 or @rlad>20030901)		
-	190	438/750.ccls.	USPAT;	2004/08/19 11:21
			US-PGPUB	
-	0	1 (((	USPAT;	2004/08/19 11:22
		insulator or oxide or IMD or FSG or USG or TEOS)) with 438/750.ccls.	US-PGPUB	
	357	438/756.ccls.	USPAT;	2004/08/19 11:21
	557	100/100.0010.	US-PGPUB	230 77007 10 771.21
-	0	(((CMP or polishing) with (slurry with water)) with (dielectric or	USPAT;	2004/08/19 11:21
	_	insulator or oxide or IMD or FSG or USG or TEOS)) with	US-PGPUB	
		438/756.ccls.		
-	0	(((CMP or polishing) with (slurry with water)) with (dielectric or	USPAT;	2004/08/19 11:22
		insulator or oxide or IMD or FSG or USG or TEOS)) same	US-PGPUB	
_	0	438/750.ccls. (((CMP or polishing) with (slurry with water)) with (dielectric or	USPAT;	2004/08/19 11:22
-	U	insulator or oxide or IMD or FSG or USG or TEOS)) and	US-PGPUB	2007/00/19 11.22
		438/750.ccls.	30.0.00	
-	81620	438/\$.ccls.	USPAT;	2004/08/19 11:23
			US-PGPUB	
-	121	(((CMP or polishing) with (slurry with water)) with (dielectric or	USPAT;	2004/08/19 11:23
		insulator or oxide or IMD or FSG or USG or TEOS)) and	US-PGPUB	
	440	438/\$.ccls.	LICDAT.	2004/09/40 44:00
-	118	((((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS)) and	USPAT; US-PGPUB	2004/08/19 11:23
		438/\$.ccls.) not (@ad>20030901 or @rlad>20030901)	55 / 5/ 55	
		438/\$.ccis.) not (@ad>20030901 or @riad>20030901)		

-	53	(((((CMP or polishing) with (slurry with water)) with (dielectric	USPAT;	2004/08/19 11:30
	•	or insulator or oxide or IMD or FSG or USG or TEOS)) and	US-PGPUB	
		438/\$.ccls.) not (@ad>20030901 or @rlad>20030901)) not		
		((438/692.ccls. and (((CMP or polishing) with (slurry with		
		water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS))) not (@ad>20030901 or @rlad>20030901))		
	517047	semiconductor or "integrated circuit"	USPAT;	2004/08/19 11:30
-	317047	Semiconductor of integrated circuit	US-PGPUB	2004/00/13 11:50
1_	343	(((CMP or polishing) with (slurry with water)) with (dielectric or	USPAT;	2004/08/19 11:31
	010	insulator or oxide or IMD or FSG or USG or TEOS)) and	US-PGPUB	
		(semiconductor or "integrated circuit")	00 / 0. 02	
-	293	((((CMP or polishing) with (slurry with water)) with (dielectric or	USPAT;	2004/08/19 11:31
		insulator or oxide or IMD or FSG or USG or TEOS)) and	US-PGPUB	
		(semiconductor or "integrated circuit")) not (((((CMP or		
		polishing) with (slurry with water)) with (dielectric or insulator or		
		oxide or IMD or FSG or USG or TEOS)) and 438/\$.ccls.) not		
		(@ad>20030901 or @rlad>20030901)) not ((438/692.ccls. and		
		(((CMP or polishing) with (slurry with water)) with (dielectric or		
		insulator or oxide or IMD or FSG or USG or TEOS))) not		
	007	(@ad>20030901 or @rlad>20030901)))	USPAT:	2004/08/19 11:59
-	237	(((((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS)) and	US-PGPUB	2004/06/19 11.59
	ļ	(semiconductor or "integrated circuit")) not (((((CMP or	03-7-07-05	
		polishing) with (slurry with water)) with (dielectric or insulator or		
		oxide or IMD or FSG or USG or TEOS)) and 438/\$.ccls.) not	:	
		(@ad>20030901 or @rlad>20030901)) not ((438/692.ccls. and		
		(((CMP or polishing) with (slurry with water)) with (dielectric or		
		insulator or oxide or IMD or FSG or USG or TEOS))) not		
		(@ad>20030901 or @rlad>20030901)))) not ((438/692.ccls.		
		and (((CMP or polishing) with (slurry with water)) with		
		(dielectric or insulator or oxide or IMD or FSG or USG or		
		TEOS))) not (@ad>20030901 or @rlad>20030901))		
-	990	"first polishing" and "second polishing"	USPAT;	2004/08/19 12:00
	235	((CMP or poliobing) with (clure, with woter)) and ("first	US-PGPUB USPAT;	2004/08/19 12:00
-	233	((CMP or polishing) with (slurry with water)) and ("first polishing" and "second polishing")	US-PGPUB	2004/00/19 12:00
<u>-</u>	229	(((CMP or polishing) with (slurry with water)) and ("first	USPAT;	2004/08/19 12:00
		polishing" and "second polishing")) not (@ad>20030901 or	US-PGPUB	200 17007 10 12.00
		@rlad>20030901)		
-	206	(semiconductor or "integrated circuit") and ((((CMP or	USPAT;	2004/08/19 12:00
		polishing) with (slurry with water)) and ("first polishing" and	US-PGPUB	
		"second polishing")) not (@ad>20030901 or		
		@rlad>20030901))		0004/00/10 10 01
-	29	("first polishing" with slurry) and ("second polishing" with	USPAT;	2004/08/19 12:01
	28	water) (("first polishing" with slurry) and ("second polishing" with	US-PGPUB USPAT;	2004/08/19 12:01
-	28	water)) not (@ad>20030901 or @rlad>20030901)	US-PGPUB	2004/00/18 12.01
1_	139	damascene and (IMD with (FSG or USG or TEOS))	USPAT;	2004/08/20 11:37
-	133	damascene and (IND with (1 30 of 050 of 1200))	US-PGPUB	2004/00/20 11.5/
-	56874	@ad>20030901 or @rlad>20030901	USPAT;	2004/08/20 11:37
		<u> </u>	US-PGPUB	
-	138	(damascene and (IMD with (FSG or USG or TEOS))) not	USPAT;	2004/08/20 11:37
		(@ad>20030901 or @rlad>20030901)	US-PGPUB	
-	260	IMD with (CMP or polishing)	USPAT;	2004/08/20 11:37
			US-PGPUB	
-	45	((damascene and (IMD with (FSG or USG or TEOS))) not	USPAT;	2004/08/21 13:48
		(@ad>20030901 or @rlad>20030901)) and (IMD with (CMP or	US-PGPUB	
1		polishing))	LICDAT	2004/00/04 40:40
-	1	("6255201").PN.	USPAT; US-PGPUB	2004/08/21 13:48
L	L		03-PGPUB	